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Inclosure Material:

Metal all transistor

Overall Length:

0.170 inches all transistor and 0.210 inches all transistor

Terminal Length:

0.500 inches all transistor

Overall Diameter:

0.208 inches all transistor and 0.238 inches all transistor

Internal Configuration:

Field effect all transistor

Channel Polarity And Control Type (non-core):

N-channel insulated gate type all transistor

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-72 all transistor

Component Function Relationship:

Matched

Component Name And Quantity:

2 transistor

Mounting Method:

Terminal all transistor

Terminal Circle Diameter:

0.100 inches all transistor

Field Force Effect Type:

Electrostatic charge

Features Provided:

Hermetically sealed case and electrostatic sensitive

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

10.0 emitter to base voltage, floating potential, dc with collector biased in reverse direction with respect to the base all transistor and 15.0 drain to substrate voltage all transistor and 15.0 source to substrate voltage all transistor

Current Rating Per Characteristic:

50.00 milliamperes source cutoff current of standard range all transistor

Power Rating Per Characteristic:

300.0 milliwatts small-signal input power, common-collector absolute all transistor

Maximum Operating Temperature Per Measurement Point:

125.0 degrees celsius ambient air all transistor

Terminal Type And Quantity:

4 uninsulated wire lead all transistor

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fig:

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